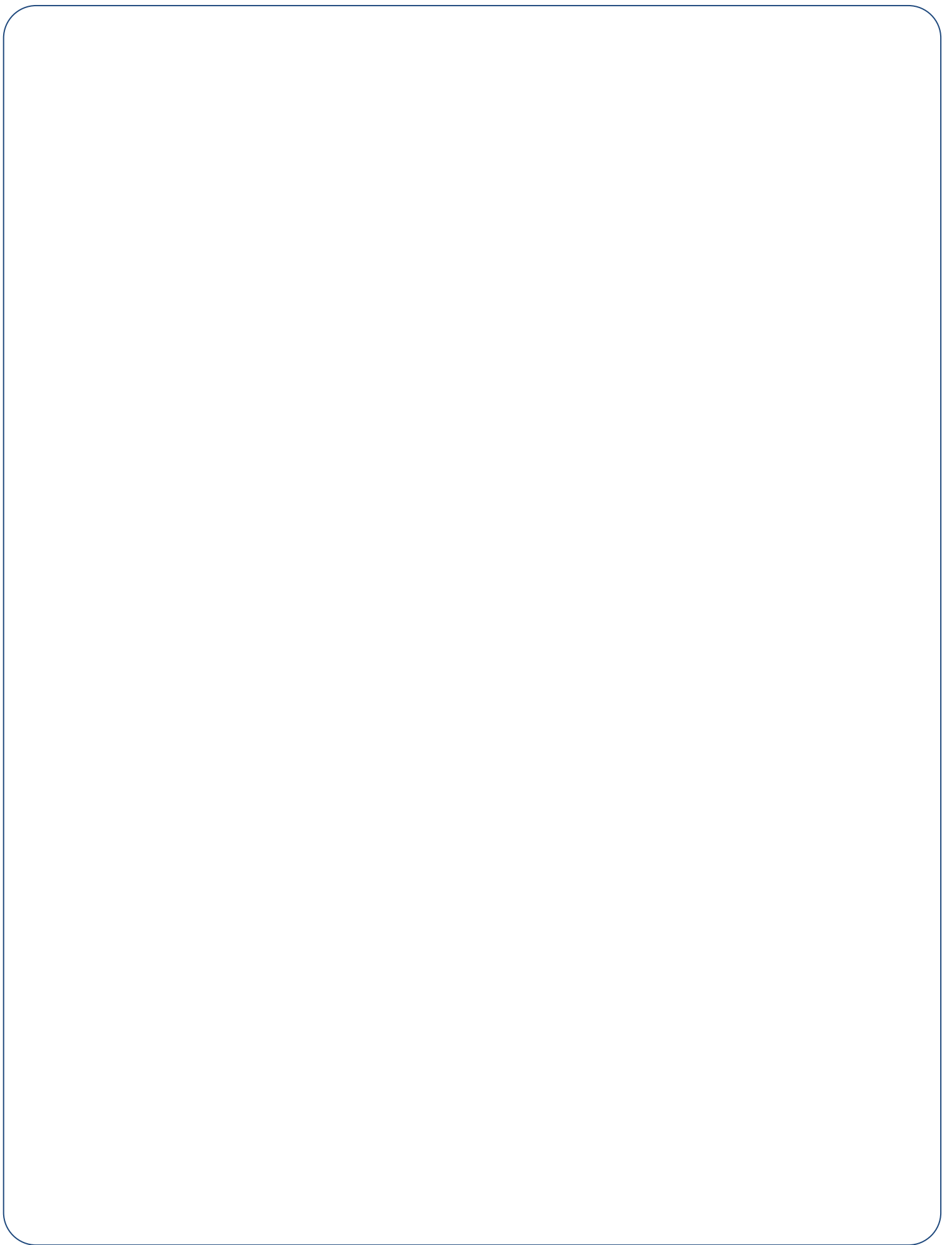




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***Storage Class Memory:  
Coming to a Datacenter Near You***

Report No. FI-NVM-SCM-1115



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## About the Authors

**Hai (Helen) Li** received her B.S. and M.S. degrees in microelectronics from Tsinghua University, Beijing, China, and Ph.D. degree from the Electrical and Computer Engineering Department at Purdue University, West Lafayette, Indiana, United States, in 2004. She is currently an Associate Professor with the Department of Electrical and Computer Engineering, University of Pittsburgh, Pittsburgh, Pennsylvania, United States. Previously, Dr. Li worked at Qualcomm Inc., Intel Corp., Seagate Technology, and Polytechnic Institute of New York University. She has extensive industry experience in circuit-level optimization and design for STT-MRAM and ReRAM technologies. Her current research focuses on emerging memory technologies, architecture/circuit/device co-design, emerging memory design, brain-inspired computing systems, hardware implementation and acceleration for machine learning, and 3D integration technology and design.

Dr. Li has authored and co-authored over 100 technical papers published in peer-reviewed journals and conferences and holds 71 granted U.S. patents. Her book “Nonvolatile Memory Design: Magnetic, Resistive, and Phase Changing” was published by CRC Press in 2011. Dr. Li received five best paper awards and five best paper nominations from ISQED, ISLPED, DATE, ISVLSI, ASPDAC, and ICCAD. She is the associate editor of TVLSI, TMSCS, and TODAES and has served as organization and technical program committee member for more than 20 international conference series. Dr. Li was the recipient of NSF CAREER award in 2012 and DARPA Young Faculty Award (YFA) in 2013.

**Stefan Slesazek** is a Senior Scientist at NaMLab GmbH, Prior to NaMLab, he was a project leader for the pre-development of new memory concepts with Qimonda Dresden (Germany) focusing on concept evaluation for 1T-DRAM. As a device engineer at Infineon Technologies Stefan worked on the module development of 3D DRAM access devices in 65nm and 46nm buried word line technology and pre-development of FinFET and floating body devices. Stefan received a Ph.D. in microelectronics from the Dresden University of Technology, Germany. His current research focuses on electrical characterization, device reliability investigation and memory concept evaluation for various memories, such as resistive memory, ferroelectric field effect transistor and emerging memristor applications.

Stefan has published more than 50 technical papers in refereed journals and conferences, filed more than 15 U.S. patents and co-authored 2 book chapters.

**Gregory Wong** is the Founder and Principal Analyst of Forward Insights. Greg has in-depth knowledge of the cost, performance and markets and applications of multi-bit per cell NOR, NROM and NAND flash memories, emerging memories and solid state drives. Greg previously held a number of management positions in strategic planning, business development and engineering at Hitachi, Siemens, ProMOS and Qimonda/Infineon. At Infineon/Qimonda, Greg was responsible for driving manufacturing efficiencies and investment planning for a DRAM fab in Taiwan. Subsequently, he became responsible for competitive intelligence and reverse engineering for flash memories focusing on flash memory vendors' strategies, process technologies, design architectures, product performance, manufacturing capabilities and costs.

Greg earned his B.A.Sc. degree in Electrical Engineering from the University of Toronto, and his M.B.A. degree from the Richard Ivey School of Business in London, Ontario.



## About NamLab

NaMLab (**N**ano-electronic **M**aterials **L**aboratory)

The research at NaMLab focuses on materials for electronic devices and new device concepts. Among these are high-k materials for capacitors, transistors and other applications, novel switching devices including memristors, nanowire based electronics as well as materials for energy harvesting devices such as solar cells.

Future nano-electronic products require the development of new materials that are not currently available. NaMLab consequently focuses its research activities on materials and applications that show the potential to offer significant advantages over materials and products used today. In addition to investigating and characterizing new materials, NaMLab is undertaking research on the integration of these materials into semiconductor products with nano-scale dimensions.

NaMLab, originally founded as a research joint venture between Qimonda AG and the TU Dresden in July 2006, has its roots in the Corporate Research Department of Infineon AG and is now owned completely by the Technical University of Dresden. NaMLab receives basic financing from the Saxon Ministry of Science and Arts (SMWK). The company benefits from excellent working conditions in its office and clean room building opened in October 2007 and located within the TU Dresden campus.

Characterization:

- physical characterization (conductive AFM, SSRM, SEM)
- electrical device characterization;
  - 200mm/300mm wafer probe stations
  - 80K – 500K temperature range
  - Analytical measurements of memory cells (lifetime, switch time , storage and deletion windows)
  - charge carrier mobility with Hall and split-C(U)
- optical characterization (FTIR ellipsometry,  $\mu$ Raman and photoluminescence)
- dielectric reliability (TDDB, BTI, SILC)
- high-k material development
  - oxides: AlO, TiO, ZrO, HfO and mixtures
  - metals: Al, Pt, Au, TiN, Ti, Ru
  - methods: ALD, MBE, PVD, evaporation

Development:

- materials for emerging memories
- high-k stacks for capacitors and transistors
- development of new memory concepts
- charge trap device development
- development of explorative devices based on silicon nano wires

## Contact

NaMLab gGmbH  
Noethnitzer Str. 64  
01187 Dresden  
Germany  
T +49.351.21.24.990-00  
F +49.351.475.83.900  
E-mail: [info@namlab.com](mailto:info@namlab.com)

**namlab**  
nanoelectronic materials laboratory

[www.namlab.com](http://www.namlab.com)

## About Forward Insights

Forward Insights provides independent, insightful market research, consulting and information services focusing on semiconductor memories and solid state storage. The company offers unparalleled depth and understanding of the strategic, market and technical complexities of the semiconductor memory landscape.

### Services

Forward Insights offers a unique and comprehensive strategic, financial, market and technical perspective on the semiconductor memory industry. The professional services offered include:

- Strategy Consulting
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### Contact

12 Appian Dr.  
North York, Ontario  
Canada M2J 2P6  
Tel.: +1-408-565-8207  
E-mail: [greg@forward-insights.com](mailto:greg@forward-insights.com)



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